

60 V, 3.8 A NPN low VCEsat transistor

20 September 2024

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS4041PT

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\sf I}_{\sf C}$ and ${\sf I}_{\sf CM}$
- + High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current			-	-	3.8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	8	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	38	66	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	E	emitter		J
3	С	collector		B
			1 2 SOT23	sym021

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4041NT	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4041NT	%BK

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

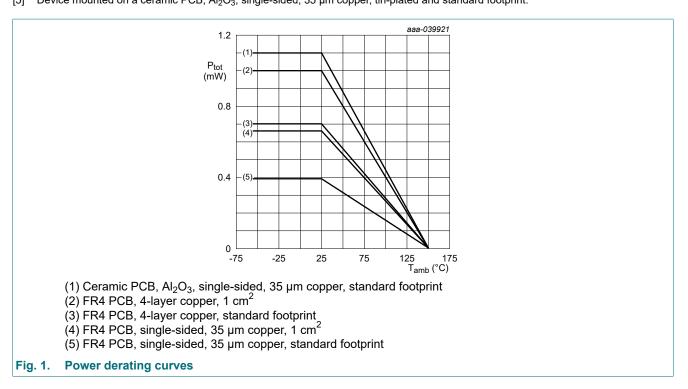
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	3.8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	А
I _B	base current			-	1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.39	W
			[2]	-	0.66	W
			[3]	-	0.7	W
			[4]	-	1	W
			[5]	-	1.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².
 [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint.



9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resist	thermal resistance from	-	[1]	-	-	320	K/W
	junction to ambient		[2]	-	-	190	K/W
		[3]	-	-	180	K/W	
	[4]	[4]	-	-	125	K/W	
	[!	[5]	-	-	115	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	62	K/W

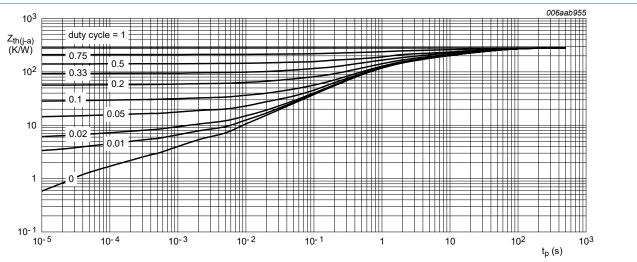
[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

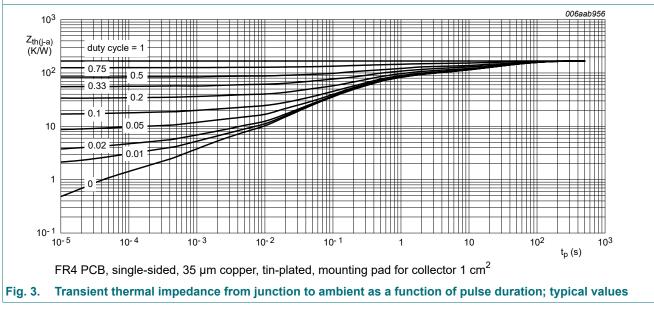
[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint.

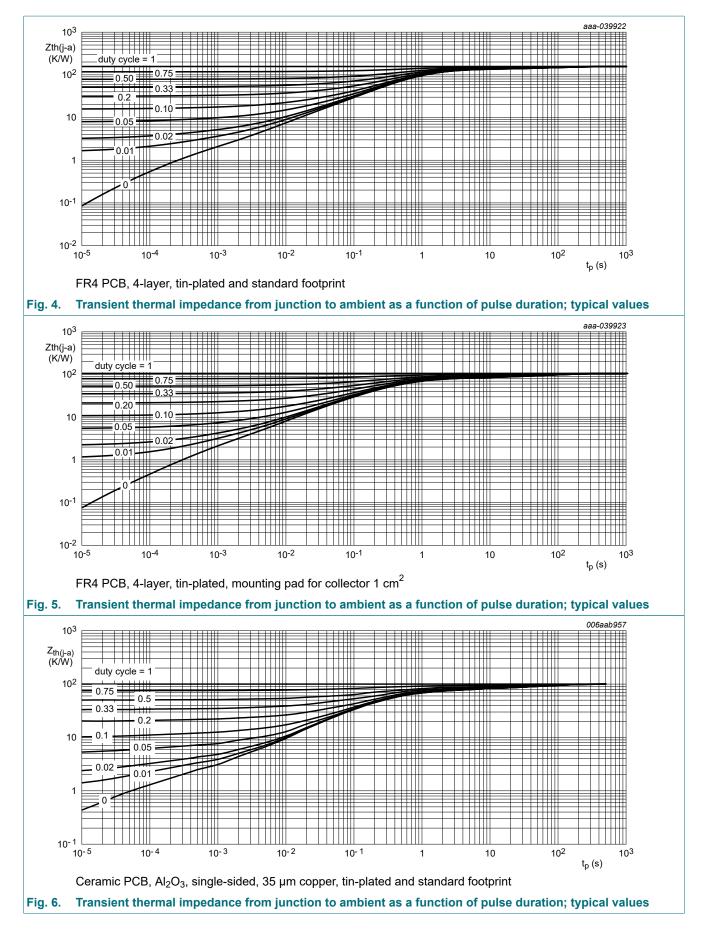


FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint





60 V, 3.8 A NPN low VCEsat transistor

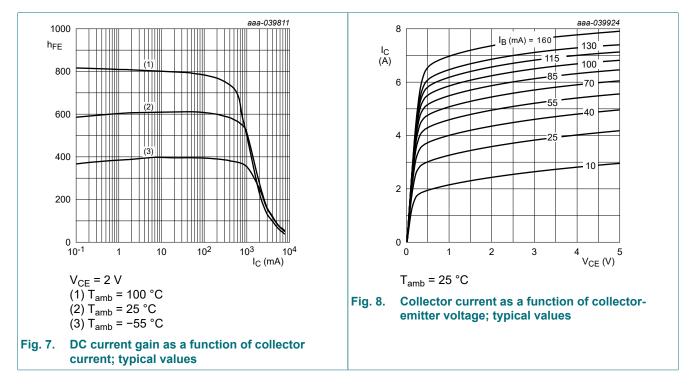


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A; T _{amb} = 25 °C	60	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0 A; T _{amb} = 25 °C	60	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 100 μA; I _C = 0 A; T _{amb} = 25 °C	5	-	-	V
I _{CBO}	collector-base cut-off	$V_{CB} = 60 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	100	nA
current		V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
CES	collector-emitter cut-off current	V_{CE} = 48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	300	500	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 1 A; pulsed; } t_{p} \texttt{\leq 300 } \mu s; \\ \delta \texttt{\leq } 0.02; T_{amb} \texttt{= 25 °C} \end{array} $	250	460	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 2 A; pulsed; } t_{p} \texttt{\leq 300 } \mu s; \\ \delta \texttt{\leq } 0.02; T_{amb} \texttt{= 25 }^\circ C \end{array} $	120	260	-	
	V_{CE} = 2 V; I _C = 4 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	30	100	-		
V _{CEsat}	CEsat collector-emitter saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	25	40	mV
		I_{C} = 1 A; I_{B} = 10 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	140	mV
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	50	80	mV
		I_{C} = 2 A; I_{B} = 40 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	110	190	mV
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	115	200	mV
		I_{C} = 4 A; I_{B} = 200 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	165	300	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	38	66	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.89	1.05	V
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1.04	1.2	V
		I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1.1	1.3	V
V _{BE}	base-emitter voltage	V_{CE} = 2 V; I _C = 2 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	-	0.8	0.9	V

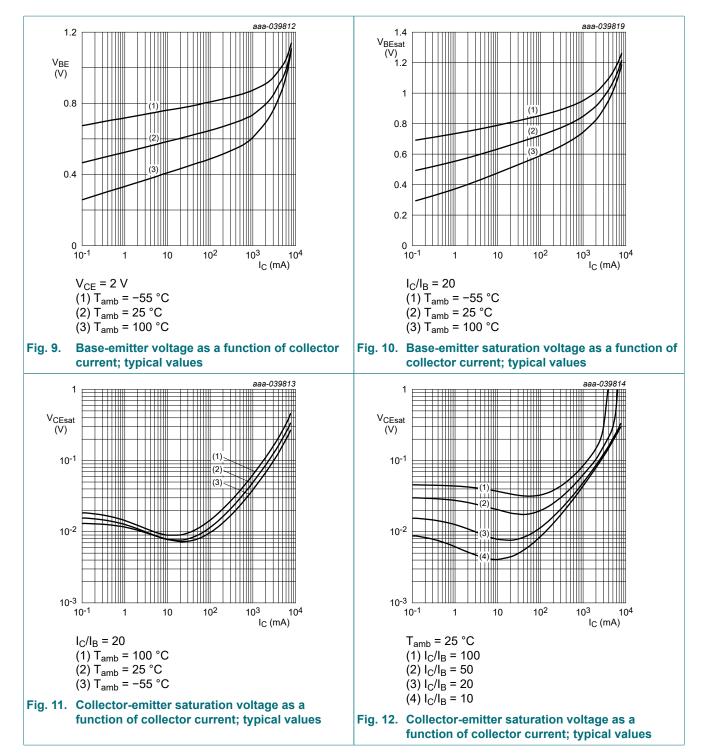
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	-	85	-	ns
t _{on}	turn-on time		-	105	-	ns
ts	storage time		-	675	-	ns
t _f	fall time		-	195	-	ns
t _{off}	turn-off time		-	870	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	155	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	15	-	pF

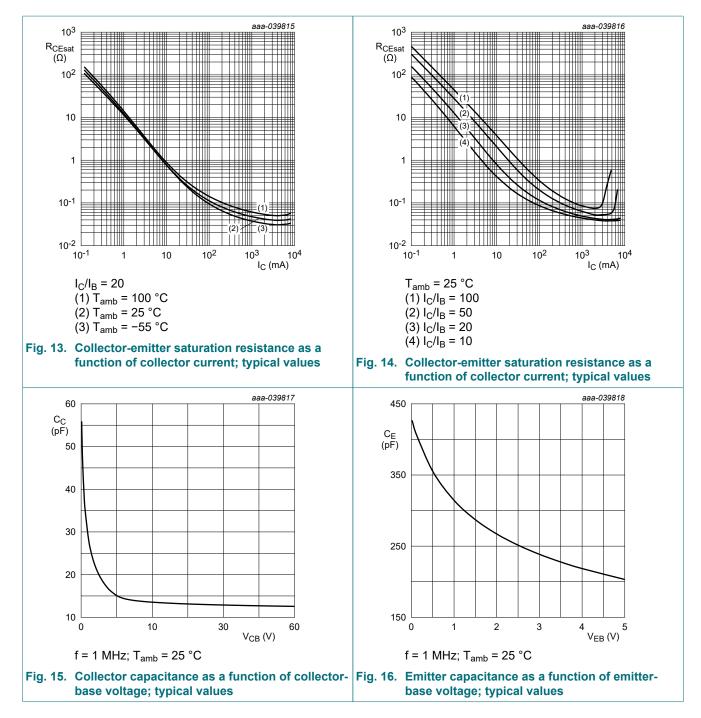


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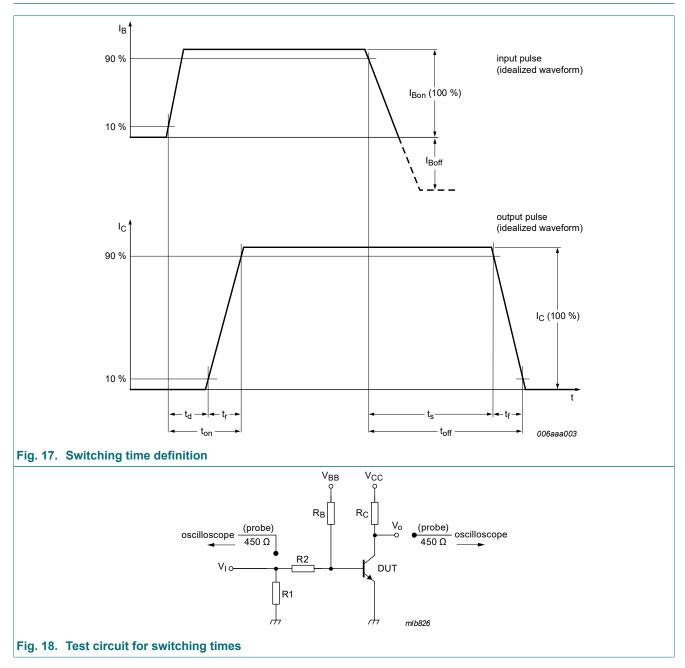
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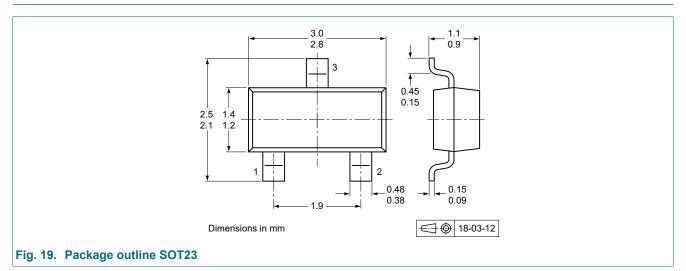
11. Test information



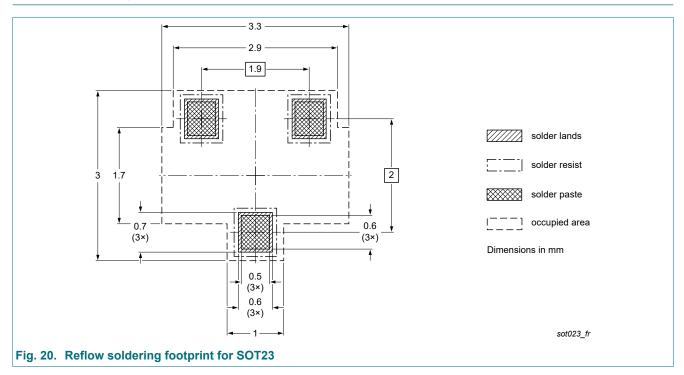
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

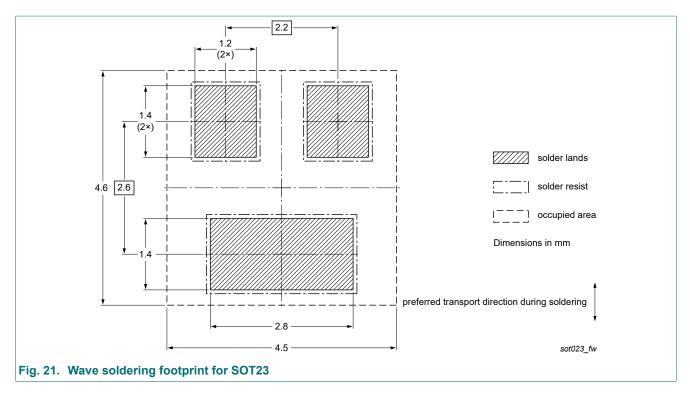
12. Package outline



13. Soldering



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PBSS4041NT

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14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4041NT v.3	20240920	Product data sheet	-	PBSS4041NT v.2		
Modifications:	New graphics a	New graphics added, graphs updated and values changed.				
PBSS4041NT v.2	20230915	Product data sheet	-	PBSS4041NT_1		
PBSS4041NT_1	20100131	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	
9. Thermal characteristics	4
10. Characteristics	6
11. Test information	10
12. Package outline	
13. Soldering	
14. Revision history	13
15. Legal information	
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